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10/17/01  
Hayes  
RECEIVED  
PATENT APPLICATION  
Do. No. 5484-53

OCT 11 2001

TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Tae-Gyoung KANG

Serial No. 09/458,506

Examiner: Nadav, O

Filed: December 9, 1999

Group Art Unit: 2811

For: LAYOUT METHOD OF SEMICONDUCTOR DEVICE

Assistant Commissioner for Patents  
Washington, D.C. 20231

### RESPONSE TO OFFICE ACTION

Responsive to the Office Action, dated March 28, 2001, please amend the application as follows.

10/10/2001 BABRAHA1 00000136 131703 09458506

01 FC:117 30.00 CH 890.00 OP

### IN THE SPECIFICATION

Replace the paragraph beginning at page 2, line 17 and ending at page 2, line 24 with the following paragraph:

a1  
As shown in Fig. 2, etching of the oxide layer through open regions of photo resist 16 produces undercut of silicon dioxide 12, as described by circles that increase in radius to the depth of silicon 10. The greater the radius of the circle, the more deeply the photo resist 16 gets undercut. The extent to which the photo resist 16 may be undercut cannot be known until the photo resist 16 is removed. But the shape of the edge of the oxide layer pattern (as shown with dot lines in Fig. 2) is a good indicator of the degree of undercut. In other words, the etching process is not uniform thereby producing undesirable process deviations. These etching process deviation also vary widely between gates having irregular gaps there between.

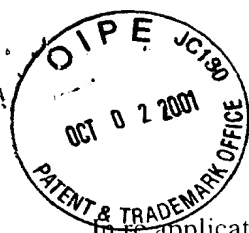
Replace the paragraph beginning at page 4, line 25 and ending at page 4, line 26 with the following paragraphs:

a2  
Fig. 5 illustrates the layout of sources, drains and gates of the transistors which make up the sense amplifier.

Fig. 6 illustrates contacts formed in the layout shown in Fig. 5.

Fig. 7 illustrates metals formed at the contacts shown in Fig. 6.

Fig. 8 illustrates contacts formed at the metals shown in Fig. 7.



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Responsive to the Office Action dated March 28, 2001, enclosed is an amendment in the above-identified application.

The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For:	Number After Amendment	Previous Number	Extra	Rate	Additional Fee
Total Claims	23	-28	0	x \$18 =	\$0
Independent Claims	6	-7	0	x \$80 =	\$0
Extension of Time - 3 <sup>rd</sup>					\$890
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$890

\*greater of twenty (20) or number for which fee has been paid

\*\*greater of three (3) or number for which fee has been paid

- ☒ Applicant petitions the Commissioner to extend the time for response. The extension fee is included and a duplicate copy of this form is enclosed.
- ☒ PTO Form 2038 authorizing credit card payment for the above-listed fees is enclosed.
- ☒ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703.

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.



20575

PATENT TRADEMARK OFFICE

Alan T. McCollom  
Reg. No. 28,881

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I HEREBY CERTIFY THAT THIS CORRESPONDENCE IS BEING DEPOSITED WITH THE UNITED STATES POSTAL SERVICE AS FIRST CLASS MAIL IN AN ENVELOPE ADDRESSED TO:  
☐ COMMISSIONER OF PATENTS AND TRADEMARKS, WASHINGTON D.C. 20231  
☒ ASSISTANT COMMISSIONER FOR PATENTS, WASHINGTON D.C. 20231  
☐ ASSISTANT COMMISSIONER FOR TRADEMARKS, 2900 CRYSTAL DRIVE, ARLINGTON VA 22202-3513  
ON 9-27-01